

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer

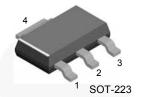


October 2014

NZT560 / NZT560A **NPN Low-Saturation Transistor**

Features

• These devices are designed with high-current gain and low-saturation voltage with collector currents up to 3 A continuous.



1. Base 2,4. Collector 3. Emitter

Ordering Information

Part Number	Marking	Package	Packing Method
NZT560	560	SOT-223 4L	Tape and Reel
NZT560A	560A	SOT-223 4L	Tape and Reel

Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current - Continuous	3	Α
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics(3)

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Max.	Unit
P _D	Total Power Dissipation	1	W
	Derate Above 25°C	8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	°C/W

Note:

3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions		Min.	Max.	Unit
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$		60		٧
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$		80		٧
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$		5		V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = 30 \text{ V, } I_{E} = 0$			100	nA
		V _{CB} = 30 V, I _E = 0, T _A = 100°C			10	μΑ
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 4 V, I _C = 0			100	nA
		I _C = 100 mA, V _{CE} = 2 V		70		
h _{FE}	DC Current Gain ⁽⁴⁾	I _C = 500 mA, V _{CE} = 2 V	NZT560	100	300	
			NZT560A	250	550	
		I _C = 1 A, V _{CE} = 2 V		80		
		I _C = 3 A, V _{CE} = 2 V		25		
V _{CE} (sat)	Collector-Emitter Saturation Voltage ⁽⁴⁾	I _C = 1 A, I _B = 100 mA			300	
		$I_{\rm C} = 3 \text{ A}, I_{\rm B} = 300 \text{ mA}$	NZT560		450	mV
			NZT560A		400	
V _{BE} (sat)	Base-Emitter Saturation Voltage ⁽⁴⁾	I _C = 1 A, I _B = 100 mA			1.25	V
V _{BE} (on)	Base-Emitter On Voltage ⁽⁴⁾ $I_C = 1 \text{ A}, V_{CE} = 2 \text{ V}$		7		1	V
C _{obo}	Output Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$			30	pF	
f _T	Transition Frequency	I _C = 100 mA, V _{CE} = 5 V, f = 100 MHz		75		MHz

Note:

4. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2.0%

Typical Performance Characteristics

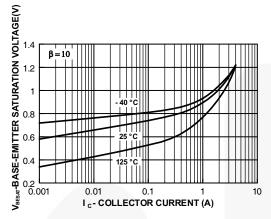


Figure 1. Base-Emitter Saturation Voltage vs. Collector Current

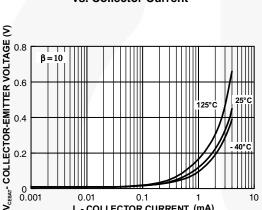


Figure 3. Collector-Emitter Saturation Voltage vs. Collector Current

0.1

I_C- COLLECTOR CURRENT (mA)

0.01

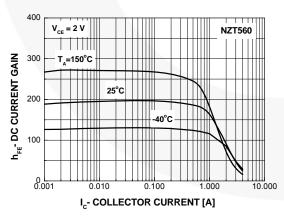


Figure 5. Current Gain vs. Collector Current

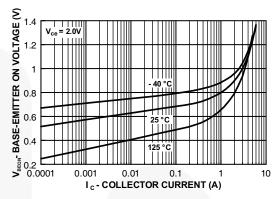


Figure 2. Base-Emitter On Voltage vs. Collector Current

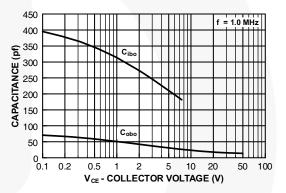


Figure 4. Input / Output Capacitance vs. Reverse Bias Voltage

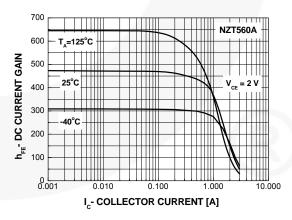
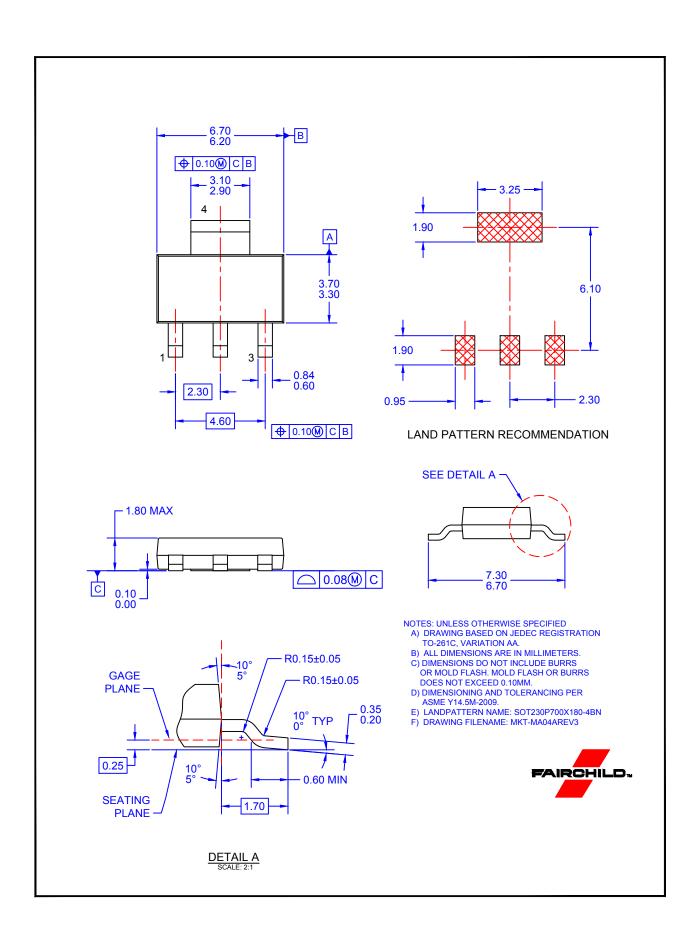


Figure 6. Current Gain vs. Collector Current

0.001



ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative